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L17: Entry 6 of 6

File: DWPI

Jan 10, 2002

DERWENT-ACC-NO: 2002-486899
DERWENT-WEEK: 200252
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TITLE: Etching silicon oxide layer

INVENTOR: KIM, D H; KWAK, H S

PATENT-ASSIGNEE: HYNIX SEMICONDUCTOR INC (HYNIN)

PRIORITY-DATA: 2000KR-0037033 (June 30, 2000)

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
<input type="checkbox"/> KR 2002002747 A	January 10, 2002		001	H01L021/316

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
KR2002002747A	June 30, 2000	2000KR-0037033	

INT-CL (IPC): [H01 L 21/316](#)

ABSTRACTED-PUB-NO: KR2002002747A

BASIC-ABSTRACT:

NOVELTY - A method for etching a silicon oxide layer is provided to improve hydrophilicity regarding a wafer, to decrease a contact angle of etchant and to reduce particles, by adding dimethylformamide(DMF) to a buffered oxide etchant(BOE) solution such that the DMF is well soluble as surfactant and has a stable characteristic and by etching the silicon oxide layer.

DETAILED DESCRIPTION - The silicon oxide layer formed on the wafer is etched by using wet etchant including DMF. The wet etchant is a BOE solution. DMF is a liquid state at a room temperature so that an etch rate does not change according to an additive quantity.

ABSTRACTED-PUB-NO: KR2002002747A

EQUIVALENT-ABSTRACTS:

CHOSEN-DRAWING: Dwg.1/10

DERWENT-CLASS: L03 U11
CPI-CODES: L04-C07C1; L04-C12A;

EPI-CODES: U11-A10; U11-C05B7; U11-C07B; U11-C07C3;

[Previous Doc](#)

[Next Doc](#)

[Go to Doc#](#)